



## 2SA1365 (3CG1365)

## 硅 PNP 半导体三极管/SILICON PNP TRANSISTOR

用途：用于小型马达驱动、继电器及电源驱动。

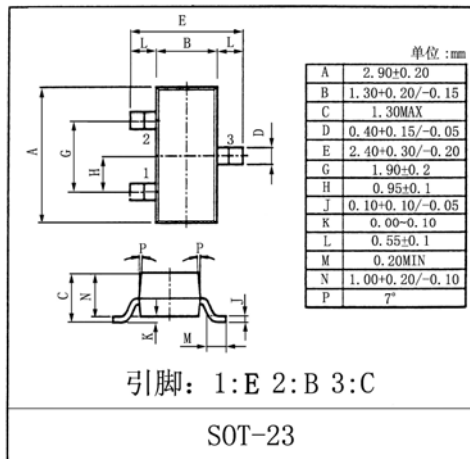
Purpose: Small type motor drive, relay drive, power supply.

特点：饱和压降小，直流电流增益高、线性好，集电极电流大，特征频率高。

Features: Low collector to emitter saturation voltage, excellent linearity of DC forward current Gain, high collector current, high gain band width product.

极限参数/Absolute maximum ratings (Ta=25°C)

参数符号 Symbol	数值 Rating	单位 Unit
V <sub>CB0</sub>	-25	V
V <sub>CE0</sub>	-20	V
V <sub>EBO</sub>	-4.0	V
I <sub>C</sub>	-700	mA
I <sub>CM</sub>	-1.0	A
P <sub>C</sub>	150	mW
T <sub>j</sub>	150	°C
T <sub>stg</sub>	-55~150	°C



电性能参数/Electrical characteristics (Ta=25°C)

参数符号 Symbol	测试条件 Test condition		数值 Rating			单位 Unit
			最小值 Min	典型值 Typ	最大值 Max	
V <sub>CB0</sub>	I <sub>C</sub> = -10 μA	I <sub>E</sub> = 0	-25			V
V <sub>CE0</sub>	I <sub>C</sub> = -100 μA	R <sub>BE</sub> = ∞	-20			V
V <sub>EBO</sub>	I <sub>E</sub> = -10 μA	I <sub>C</sub> = 0	-4.0			V
I <sub>CB0</sub>	V <sub>CB</sub> = -25V	I <sub>E</sub> = 0			-1.0	μA
I <sub>EBO</sub>	V <sub>EB</sub> = -2.0V	I <sub>C</sub> = 0			-1.0	μA
h <sub>FE</sub>	V <sub>CE</sub> = -4.0V	I <sub>C</sub> = -100mA	150		800	
V <sub>CE(sat)</sub>	I <sub>C</sub> = -500mA	I <sub>B</sub> = -25mA		-0.2	-0.5	V
f <sub>T</sub>	V <sub>CE</sub> = -6.0V	I <sub>E</sub> = 10mA		180		MHz

h<sub>FE</sub> 分档、印章/h<sub>FE</sub> Classifications、Marking:

h <sub>FE</sub> 分档 h <sub>FE</sub> Classifications	E	F	G
h <sub>FE</sub> 范围 h <sub>FE</sub> Range	150~300	250~500	400~800
印章 Marking	HAE	HAF	HAG

